

FORM PTO-1449 SAMUELS, GAUTHIER & STENS LLP
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ATTORNEY DOCKET NO. 596

SERIAL NO. 09/884.172

Fitzgerald et al.
APPLICANT

Unknown
GROUP 2812

6/19/01
FILING DATE

Unknown
EXAMINER Lathin

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

AUG 01 2001

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U.S. PATENT DOCUMENTS

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>E</i>	AA	4,710,788	12/1/87	Dambkes et al.	X	X	12/1/86
<i>E</i>	AB	5,241,197	8/31/93	Murakami et al.			9/13/91
<i>E</i>	AC	5,534,713	6/9/96	Ismail et al.			5/20/94
<i>C</i>	AD	5,777,347	7/7/98	Bartelink			6/18/97
<i>E</i>	AE	5,808,344	9/15/98	Ismail et al.			2/4/97
<i>E</i>	AF	5,906,951	5/25/99	Chu et al.			4/30/97
<i>E</i>	AG	6,013,134	1/11/00	Chu et al.			2/18/98
<i>E</i>	AH	6,059,895	5/9/00	Chu et al.			5/13/99
<i>E</i>	AI	6,111,367	8/29/00	Fischer et al.			5/4/98
<i>E</i>	AJ	6,107,653	8/22/00	Fitzgerald			6/23/98

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AK						
	AL						
	AM						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
<i>E</i>	AN	J. Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1995, pgs: 1-205
<i>E</i>	AO	"Technology for SiGe Heterostructure-Based CMOS Devices" by Mark Albert Armstrong; PhD Thesis, Massachusetts Institute of Technology, 1999; pgs: 1-154
<i>E</i>	AP	"Application of Silicon-Based Heterostructures To Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors" by Kern Rim; PhD Thesis, Stanford University, 1999; pgs: 1-184
<i>E</i>	AQ	"Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's"; Rim et al.; IEEE Transactions on Electron Devices, Vol. 47, No. 7, July 2000; pgs: 1406-1415
<i>E</i>	AR	"Enhanced Hole Mobilities in Surface-channel Strained-Si p-MOSFET's"; Rim et al.; Solid State Electronics Laboratory, Stanford University, Stanford, CA 94305; pgs: 20.3.1-20.3.4
<i>E</i>	AS	"High-Mobility Strained-Si PMOSFET's"; Nayak et al.; IEEE Transactions On Electron Devices, Vol. 43, No. 10, October 1996; pgs: 1709-1716
<i>E</i>	AT	"Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; by Mizuno et al.; IEEE Electron Device Letters, Vol. 21, No. 5, May 2000; pgs: 230-232

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Fitzgerald et al.
APPLICANTUnknown
GROUP 28126/19/01
FILING DATEUnknown
EXAMINER Lathin

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

U.S. PATENT DOCUMENTS

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Q	AA	6,111,267	8/29/00	Fischer et al.			5/4/98
	AB						
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	AI						
	AJ						

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